

## Supporting Information

**A multi-dimensional and level-by-level assembly strategy for  
constructing flexible and sandwich-type nanoheterostructures for  
high-performance electromagnetic interference shielding**

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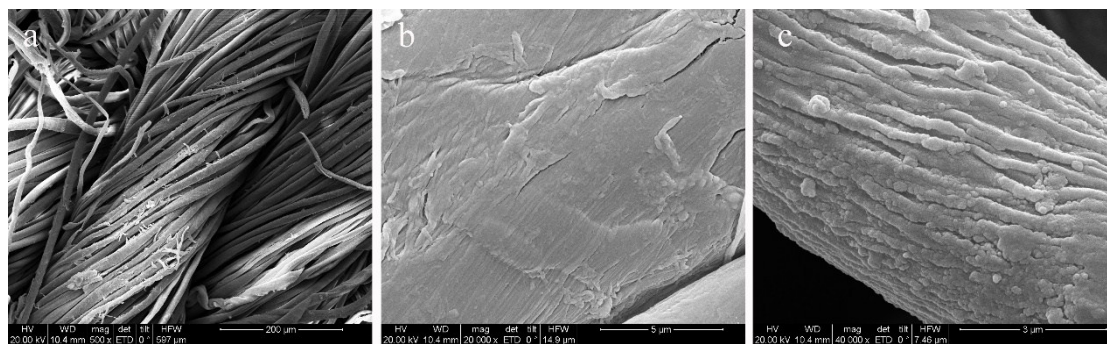
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## 1. SEM image of cotton cloth

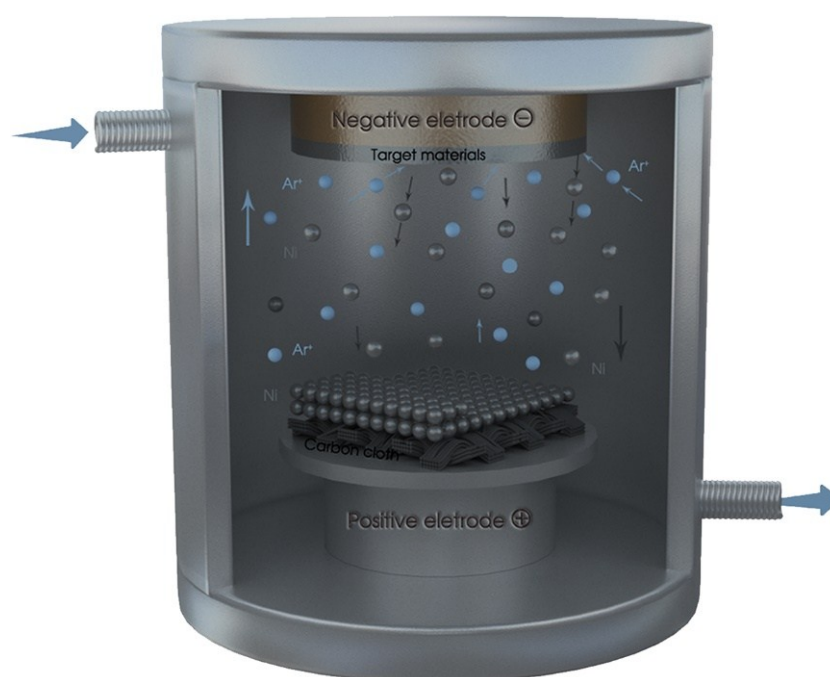


**Figure S1.** SEM images of the cotton cloth (a, b) and CFs (c).

By comparing [Fig. S1a-b](#) and [1c](#), we can find that the pyrolysis decreases the fiber diameter and transforms the smooth surface of cotton fibers to the rough surface of CFs.

## 2. Mechanism of depositing Ni NPs onto CFs by magnetron sputtering

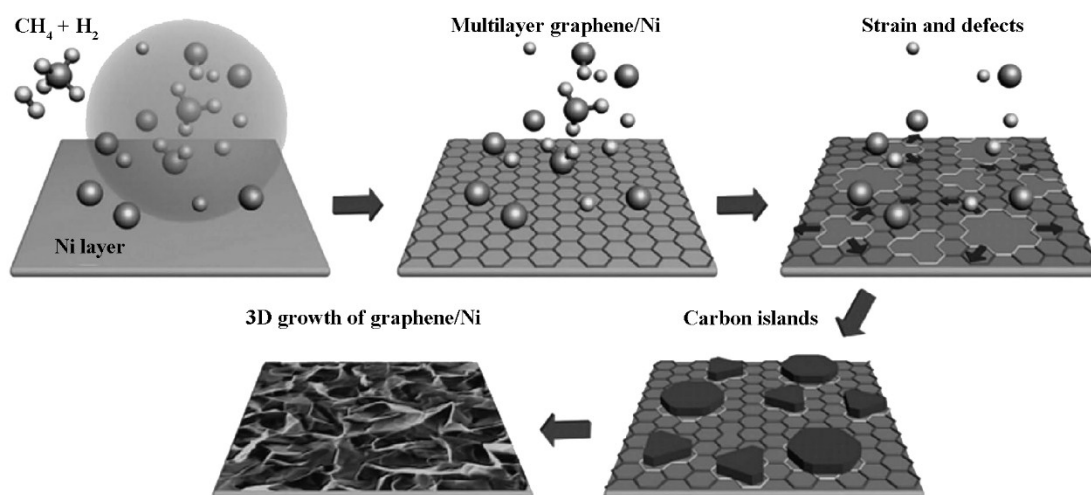
For the magnetron sputtering process (Fig. S2), inert gas atoms (Ar) were ionized and accelerated owing to the potential difference between the negatively biased target (cathode) and the anode, and the interaction of ions with the target (namely metallic Ni) surface caused the ejection (sputtering) of Ni atoms which condensed on the surface of CFs.<sup>[S1, S2]</sup> Primary merits of magnetron sputtering can be summarized as follows: (1) high deposition rates, (2) ease of sputtering any metals or alloys, (3) high-purity films, (4) high adhesion of films, (5) excellent coverage of steps and small features, (6) ability to coat heat-sensitive substrates, (7) ease of automation and (8) excellent uniformity on large-area substrates.<sup>[S3-S6]</sup>



**Figure S2.** Schematic illustration of the magnetron sputtering of metallic Ni on the surface of CFs.

### 3. Mechanism of growing DLG onto Ni NPs/CFs by PECVD

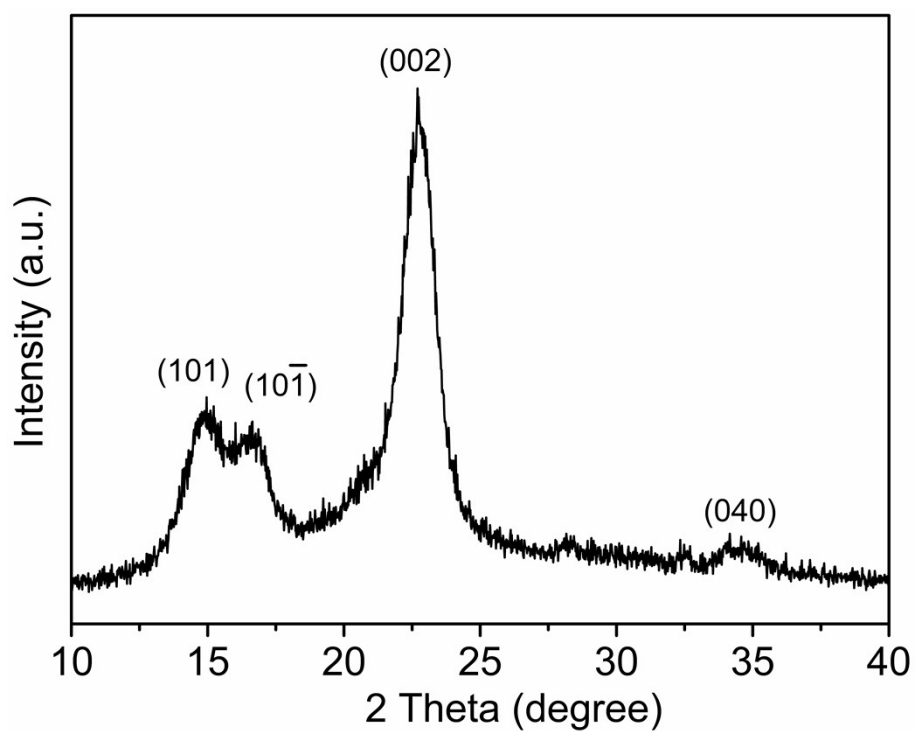
For the PECVD (Figure S3), the growth mechanism of DLG on the Ni NPs/CFs can be briefly described as follows: firstly, the trace amount of  $\text{CH}_4$  is introduced into the PECVD chamber and produces high concentration of carbon reactive radicals within a short time due to the assistance of plasma;<sup>[S7]</sup> secondly, during the PECVD of graphene, the hydrocarbon is decomposed and carbon atoms from the decomposed  $\text{CH}_4$  gas absorb on the surface of the Ni layer, leading to the growth of 2D graphene films;<sup>[S8]</sup> thirdly, the layer growth turns into vertical growth due to the strain energy in the edges and defects of initial graphene (the intermediate layer may not be able to continue to form bulk crystal and thus causes a transition from 2D complete films to 3D clusters).<sup>[S8-S10]</sup> Besides, the plasma can ensure the 3D growth of vertical graphene nanosheets, since reactive carbon radicals generated in the plasma would reach the edge frequently and thus diffuse outward.



**Figure S3.** Schematic illustration of the 3D growth process of graphene on nickel substrate in a PECVD system: (I) breakage of carbon–hydrogen bonds; (II) formation of multilayer graphene on a Ni surface; (III) strain and defects on 2D graphene film

after a period of growth; (IV) transition from 2D to 3D growth due to accumulated strain and defects; (V) development of 3D graphene clusters on a Ni substrate due to the high mobility of carbon atoms and van der Waals force between neighboring graphene sheets. Reproduced with permission [S7].

#### 4. XRD pattern of cotton cloth



**Figure S4.** XRD pattern of the cotton cloth.

The XRD pattern of the cotton cloth (the precursor of CFs) is shown in [Fig. S4](#). The cotton cloth exhibits peaks at around  $15.0^\circ$ ,  $16.6^\circ$ ,  $22.7^\circ$  and  $34.7^\circ$ , corresponding to the (101),  $(10\bar{1})$ , (002) and (040) planes of cellulose I crystal structure.<sup>[S11]</sup>

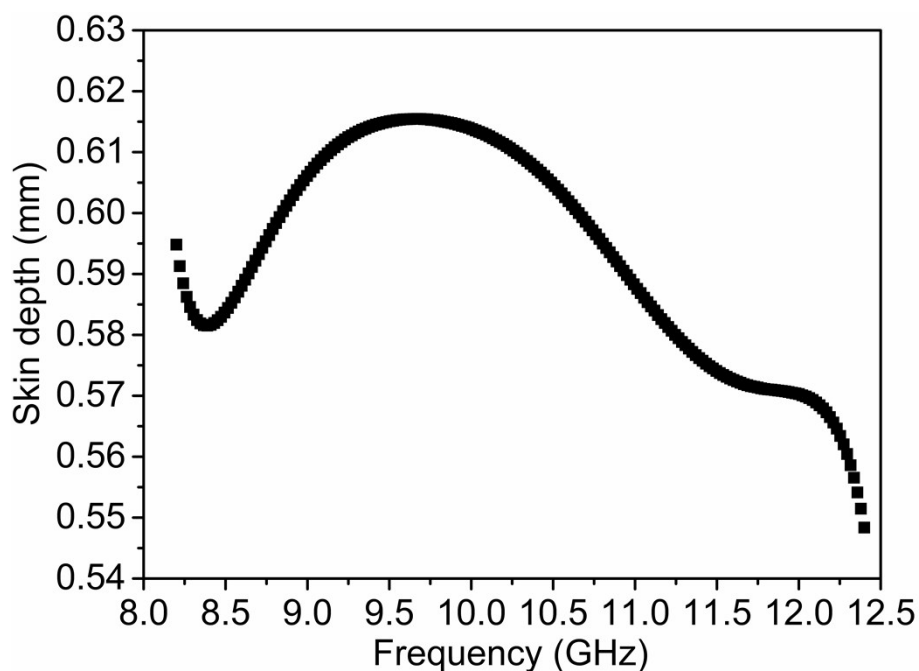
## 5. Calculation method of BET surface area of graphene in DLG/Ni NPs/CFs

The BET surface areas of Ni NPs/CFs and DLG/Ni NPs/CFs are  $12.9 \text{ m}^2 \text{ g}^{-1}$  and  $16.8 \text{ m}^2 \text{ g}^{-1}$ , respectively. Besides, their areal densities are  $7.16 \text{ mg cm}^{-2}$  and  $7.34 \text{ mg cm}^{-2}$ , respectively. The weight was accurately measured by microbalance (MS105DU, Mettler Toledo) with an accuracy of 0.01 mg. Therefore, the specific surface area of the graphene composition in DLG/Ni NPs/CFs can be roughly calculated to be  $(16.8-12.9)/[(7.34-7.16)/7.34] \approx 159 \text{ m}^2 \text{ g}^{-1}$ .



## 6. Determination of skin depth and its variation with frequency

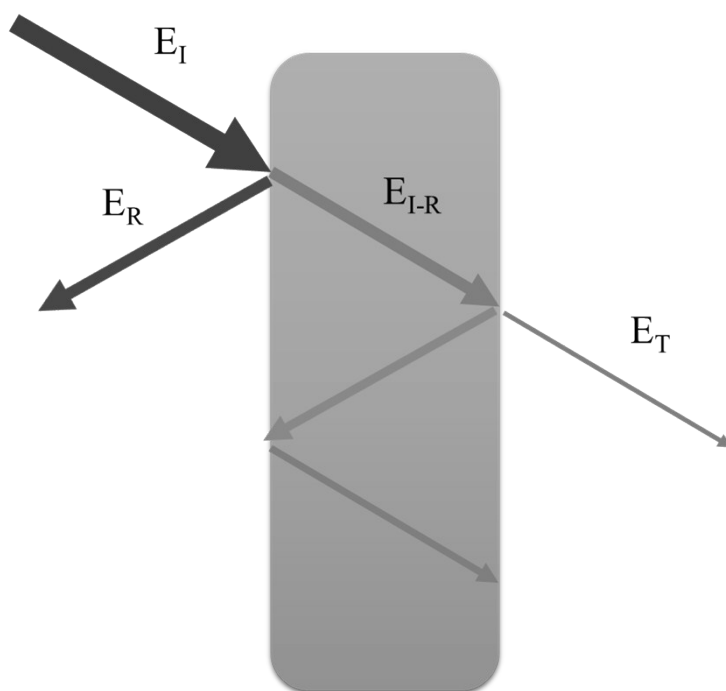
The skin depth  $\delta$  is the distance up to which the intensity of the electromagnetic wave decreases to  $1/e$  of its original strength. The  $\delta$  is related to the angular frequency  $\omega$ , relative permeability  $\mu$  and frequency dependent conductivity  $\sigma_{AC}$  by the equation,  $\delta = \sqrt{2 / \sigma_{AC} \omega \mu}$  ( $\omega = 2\pi f$ ,  $\mu = \mu_0 \mu_r$ ,  $\mu_0 = 4\pi \times 10^{-7} \text{ H m}^{-1}$ ,  $\sigma_{AC} = 2\pi f \epsilon_0 \epsilon''$ ,  $\epsilon_0 \approx 8.85 \times 10^{-12} \text{ F m}^{-1}$ ,  $\epsilon''$  is the imaginary part of complex permittivity  $\epsilon_r$ ,  $\mu_r$  is the complex permeability).<sup>[S12]</sup> The plot of  $\delta$  versus frequency in the range of 8.2–12.4 GHz is presented in Fig. S5. The skin depth  $\delta$  for DLG/Ni NPs/CFs is calculated to be 0.55–0.62 mm, meaning that this composite should have a thickness greater than this range.



**Figure S5.** Skin depth  $\delta$  of DLG/Ni NPs/CFs versus frequency in the range of 8.2–12.4 GHz (X-band).

## 7. Schematic of EMI shielding mechanism and calculation formulas of $SE_{total}$ ,

$SE_A$  and  $SE_R$



**Figure S6.** Schematic diagram of EMI shielding mechanism in an electrical conductor.

When an electromagnetic plane wave ( $E_I$ ) strikes a monolithic conductive material, two waves will be created at the external surface, namely a reflected wave ( $E_R$ ) and a transmitted wave ( $E_{I-R}$ ), as shown in Fig. S6. As the transmitted wave from the external surface ( $E_{I-R}$ ) travels in the conductive shield, the strength of the wave exponentially decreases due to absorption (multiple reflections). The absorbed energy is dissipated as heat. Once the wave reaches the second surface of the shield, a portion of the wave will pass through the surface ( $E_T$ ) and a portion will be reflected into the first surface.<sup>[S13]</sup>

EMI shielding property is evaluated by shielding effectiveness expressed in decibels (dB) over the frequency range of 8.2–12.4 GHz (X-band). A higher decibel

level reveals less energy transmitted through shielding materials. The total shielding effectiveness ( $SE_{\text{total}}$ ) can be expressed as:<sup>[S14]</sup>

$$SE_{\text{total}}(\text{dB}) = 10 \log \frac{P_i}{P_t} = SE_A + SE_R + SE_M \quad (1)$$

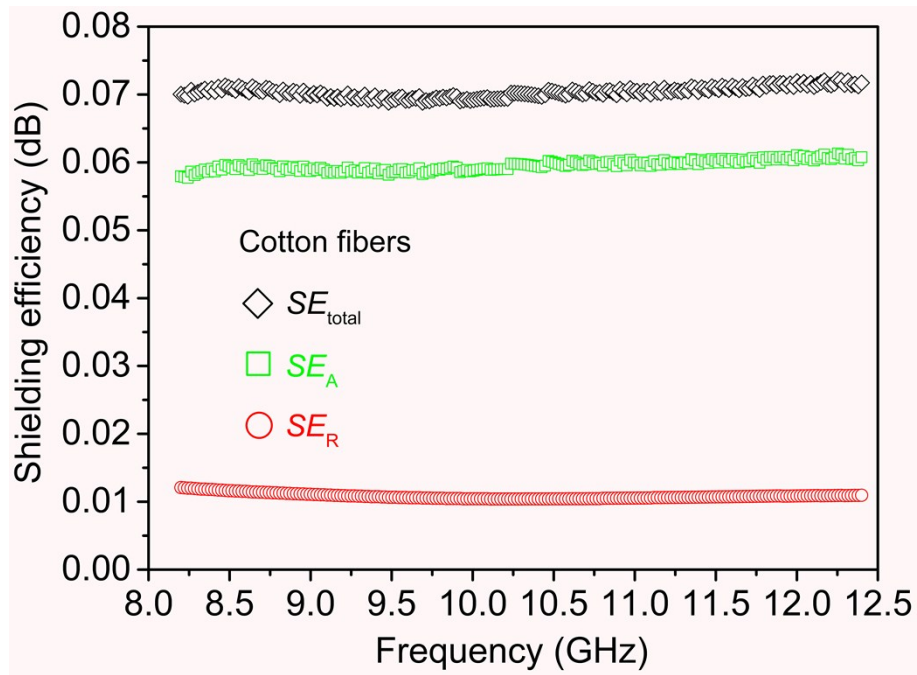
where  $P_i$  and  $P_t$  are the incident and transmitted electromagnetic power, respectively.  $SE_R$  and  $SE_A$  are the shielding effectiveness from reflection and absorption, respectively.  $SE_M$  is multiple reflection effectiveness inside the material, which can be negligible when  $SE_{\text{total}} > 15$  dB. Besides,  $SE_R$  and  $SE_A$  can be described as:<sup>[S15]</sup>

$$SE_R = -10 \log(1 - R) \quad (2)$$

$$SE_A = -10 \log[T / (1 - R)] \quad (3)$$

where  $R$  and  $T$  are reflected power and transmitted power, respectively.  $R$  and  $T$  are calculated based on the  $S$ -parameters obtained from the vector network analyzer as follows:  $R = |S_{11}|^2 = |S_{22}|^2$  and  $T = |S_{12}|^2 = |S_{21}|^2$ ,<sup>[S16]</sup> respectively.

### 8. $SE_{total}$ , $SE_A$ and $SE_R$ values of cotton fibers



**Figure S7.**  $SE_{total}$ ,  $SE_A$  and  $SE_R$  values of the cotton fibers.

The low  $SE_{total}$  of 0.07 dB is attributed to its ignorable magnetic permeability and electrical conductivity which are both decisive for EMI shielding.<sup>[S17]</sup>

## 9. Classification of electromagnetic shielding textiles

**Table S1.** Classification of electromagnetic shielding textiles. [S18, S19]

Type	Grade	$SE^I$ (dB)	Classification	$ES^{II}$ (%)
Class I Professional use <sup>III</sup>	AAAAA	$SE > 60$	Excellent	$ES > 99.9999\%$
	AAAA	$60 \geq SE > 50$	Very good	$99.9999\% \geq ES > 99.999\%$
	AAA	$50 \geq SE > 40$	good	$99.999\% \geq ES > 99.99\%$
	AA	$40 \geq SE > 30$	Moderate	$99.99\% \geq ES > 99.9\%$
	A	$30 \geq SE > 20$	Fair	$99.9\% \geq ES > 99.0\%$
Class II General use <sup>IV</sup>	AAAAA	$SE > 30$	Excellent	$ES > 99.9\%$
	AAAA	$30 \geq SE > 20$	Very good	$99.9\% \geq ES > 99.0\%$
	AAA	$20 \geq SE > 10$	good	$99.0\% \geq ES > 90.0\%$
	AA	$10 \geq SE > 7$	Moderate	$90\% \geq ES > 80\%$
	A	$7 \geq SE > 5$	Fair	$80\% \geq ES > 70\%$

<sup>I</sup>:  $SE$  = Shielding Effectiveness (dB); <sup>II</sup>:  $ES$  = Percentage of Electromagnetic Shielding (%); <sup>III</sup>: medical equipment, quarantine material, professional security uniform for electronic manufacturer, electronic kit, or other new applications; <sup>IV</sup>: casual wear, office uniform, maternity dress, apron, consumptive electronic products, and communication related products, or other new applications.

10.  $\epsilon'$ ,  $\epsilon''$ ,  $\mu'$  and  $\mu''$  values of DLG/Ni NPs/CFs in the range of X-band

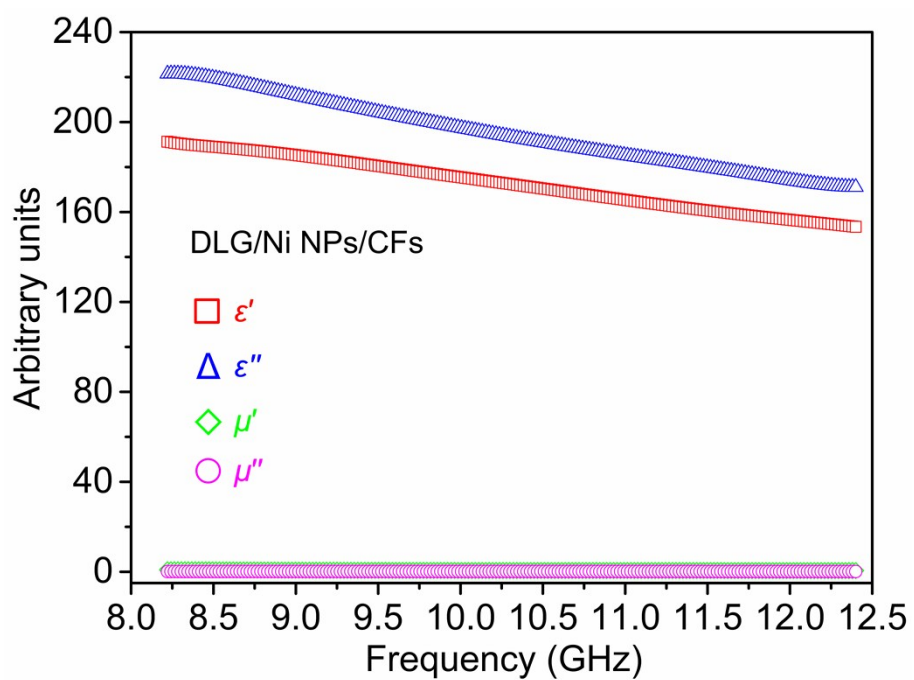


Figure S8.  $\epsilon'$ ,  $\epsilon''$ ,  $\mu'$  and  $\mu''$  values of DLG/Ni NPs/CFs in the range of X-band (8.2–12.4 GHz).

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